

NPN switching transistor

PXT2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- General purpose switching and linear amplification.

DESCRIPTION

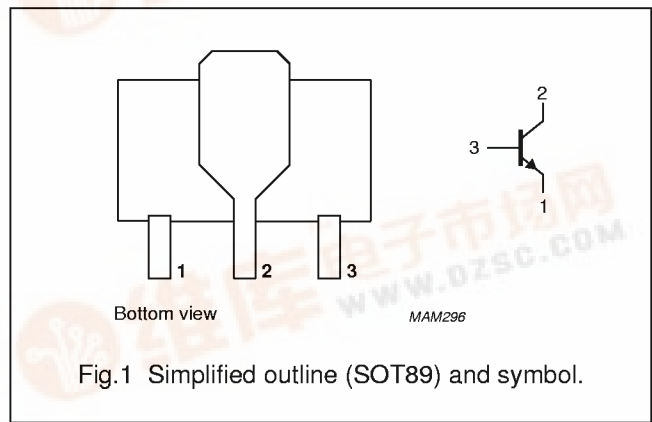
NPN switching transistor in a SOT89 plastic package.
PNP complement: PXT2907A.

MARKING

TYPE NUMBER	MARKING CODE
PXT2222A	p1P

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	75	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	600	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1	–	1.25	W
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 6 cm².
For other mounting conditions, see “Thermal considerations for SOT89 in the General Part of associated Handbook”.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	100	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		20	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 6 cm².
For other mounting conditions, see "Thermal considerations for SOT89 in the General Part of associated Handbook".

CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

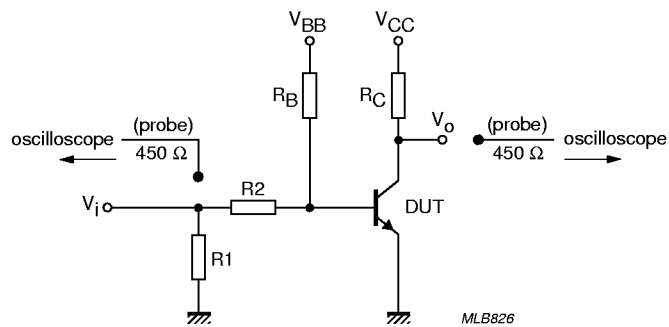
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 125\text{ }^\circ\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{BE} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$	35	–	
		$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	50	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	–	
		$I_C = 10\text{ mA}; V_C = 10\text{ V}; T_{amb} = -55\text{ }^\circ\text{C}$	35	–	
		$I_C = 150\text{ mA}; V_{CE} = 1\text{ V}$	50	–	
		$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$	100	300	
		$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}$	40	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	300	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	0.6	1.2	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	2	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	8	pF
C_e	emitter capacitance	$I_C = I_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	25	pF
f_T	transition frequency	$I_C = 20\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	300	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	4	dB

Switching times (between 10% and 90% levels); (see Fig.2)

t_{on}	turn-on time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA};$ $I_{Boff} = -15\text{ mA}$	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

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$V_i = 9.5 \text{ V}$; $T = 500 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_f \leq 3 \text{ ns}$.
 $R_1 = 68 \text{ } \Omega$; $R_2 = 325 \text{ } \Omega$; $R_B = 325 \text{ } \Omega$; $R_C = 160 \text{ } \Omega$.
 $V_{BB} = -3.5 \text{ V}$; $V_{CC} = 29.5 \text{ V}$.
Oscilloscope: input impedance $Z_i = 50 \text{ } \Omega$.

Fig.2 Test circuit for switching times.

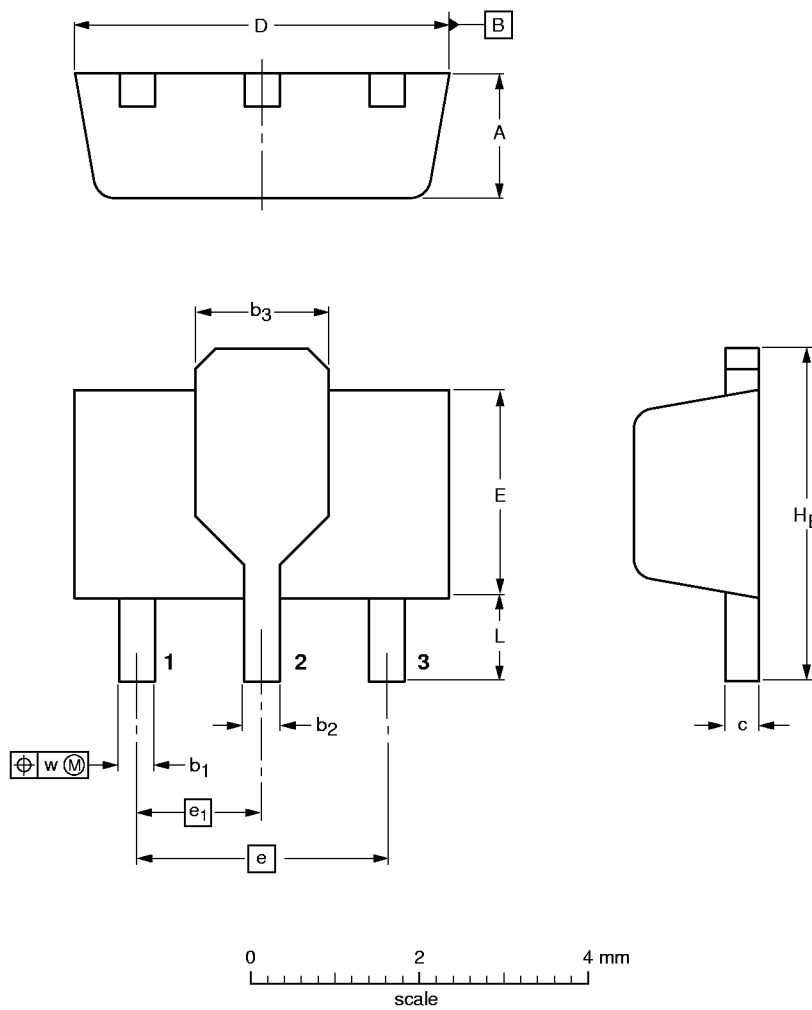
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b ₁	b ₂	b ₃	c	D	E	e	e ₁	H _E	L min.	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.37	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	0.8	0.13

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT89						97-02-28